

## Features

- $BV_{CEO} > 100V$
- Small Form Factor Thermally Efficient Package. Enables Higher Density End Products
- $I_C = 2A$  High Continuous Current
- $I_{CM} = 6A$  Peak Pulse Current
- Low Saturation Voltage  $V_{CE(SAT)} < 250mV @ 1A$
- Complementary PNP Type: DXTP07100BFG
- Rated to  $+175^{\circ}C$ —Ideal for High Temperature Environment
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

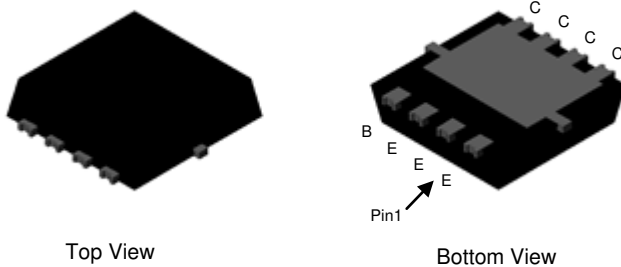
## Mechanical Data

- Case: PowerDI<sup>®</sup> 3333-8
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Weight: 0.03 grams (Approximate)

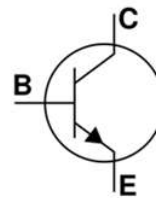
## Applications

- Load Switch
- Linear Regulator
- MOSFET or IGBT Gate Driving

PowerDI3333-8 (SWP) (Type UX)



Equivalent Circuit



Device Symbol

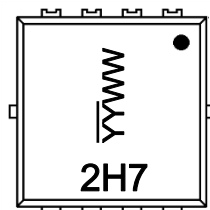
## Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTN07100BFG-7	2H7	7	12	2,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

PowerDI3333-8 (SWP) (Type UX)



- 2H7 = Product Type Marking Code
- YYWW = Date Code Marking
- YY = Last Two Digits of Year (ex: 18 = 2018)
- WW = Week Code (01 to 53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	2	A
Peak Pulse Current	I <sub>CM</sub>	6	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

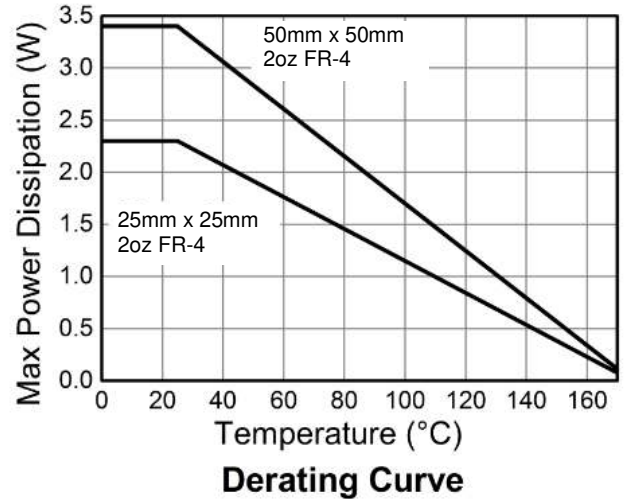
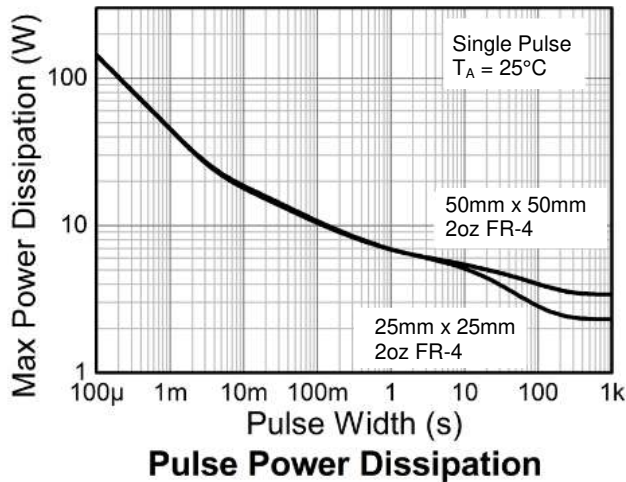
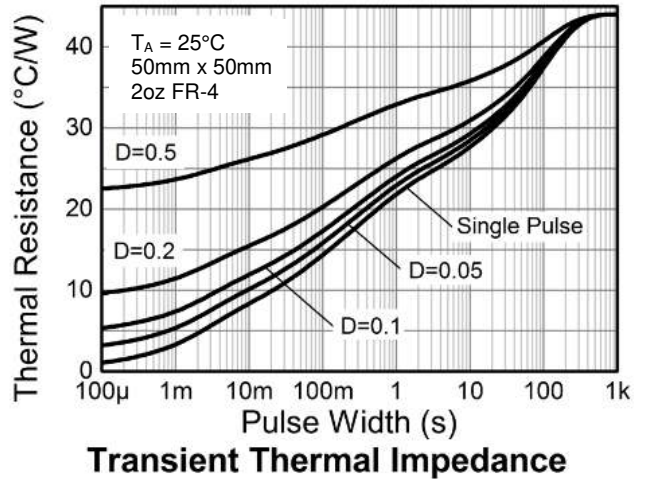
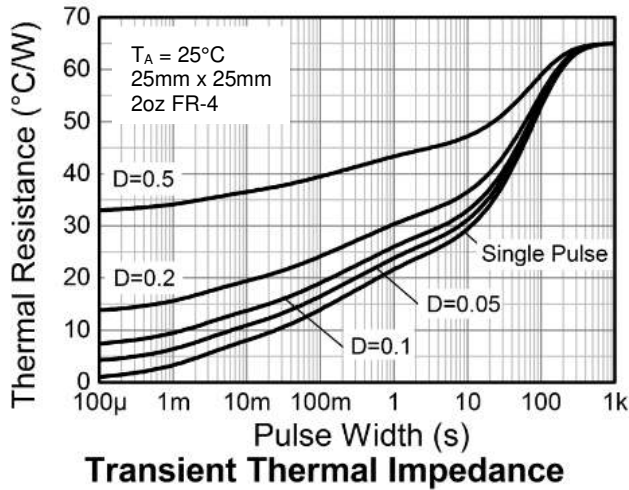
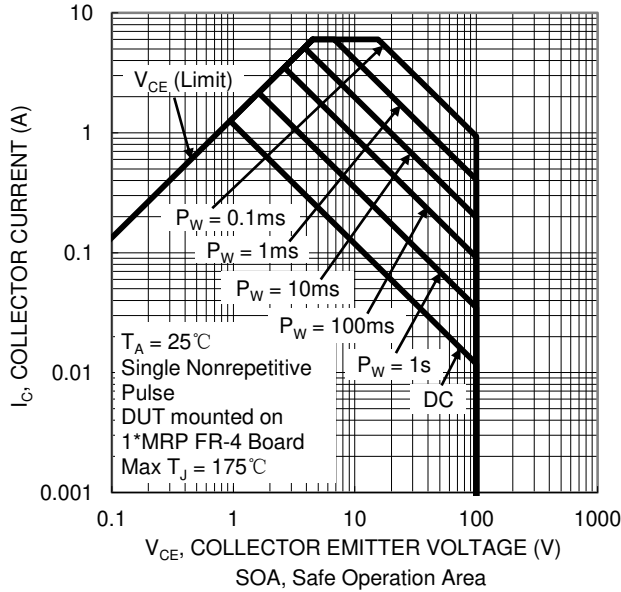
Characteristic	Symbol	Value	Unit	
Power Dissipation	P <sub>D</sub>	(Note 5)	0.9	W
		(Note 6)	2.1	W
		(Note 7)	3.1	W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Note 5)	140	°C/W
		(Note 6)	65	°C/W
		(Note 7)	44	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R <sub>θJL</sub>	8.5	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C	

**ESD Ratings** (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as Note 5, except the device is mounted on 25mm × 25mm 2oz copper.
  7. Same as Note 5, except the device is mounted on 50mm × 50mm 2oz copper.
  8. Thermal resistance from junction to solder-point (at the collector tab).
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

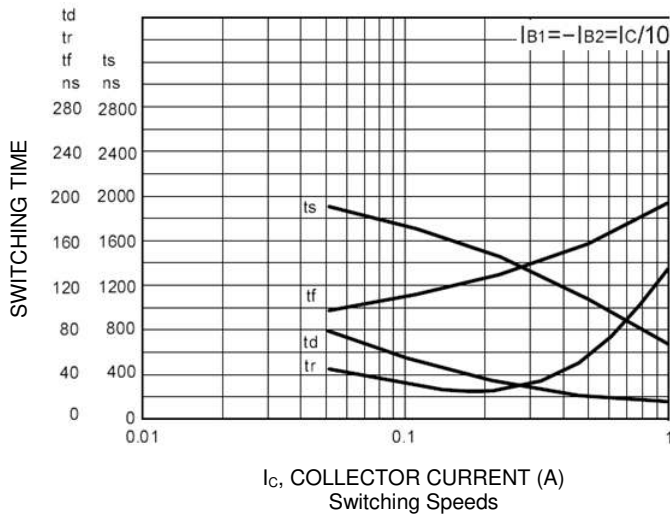
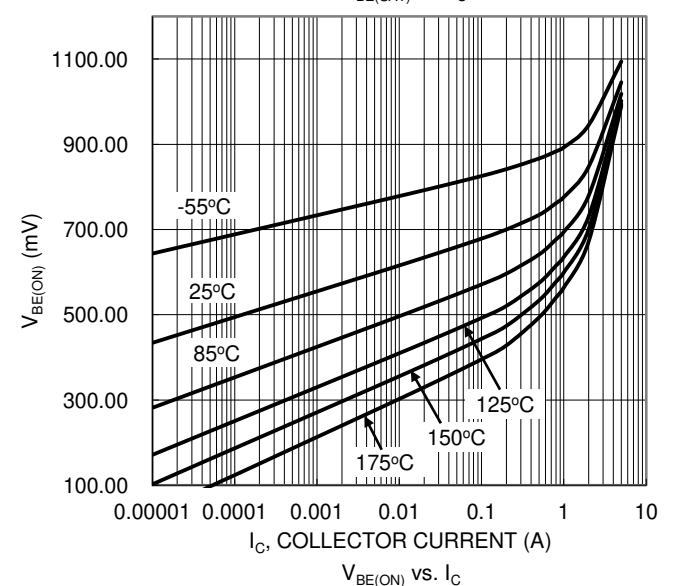
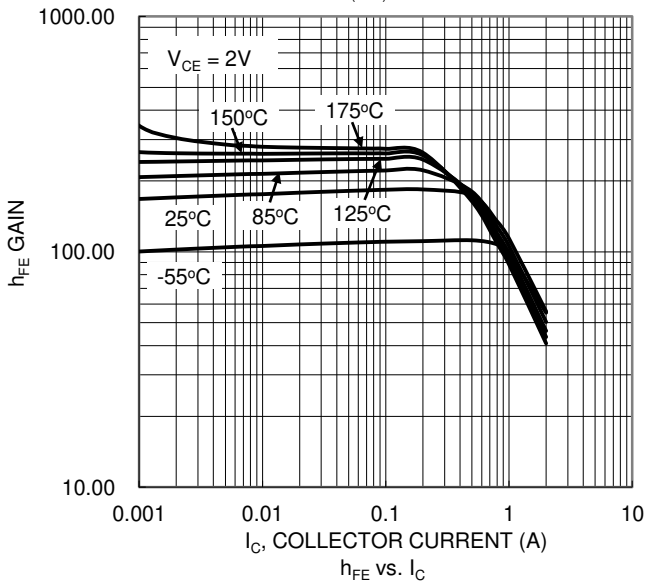
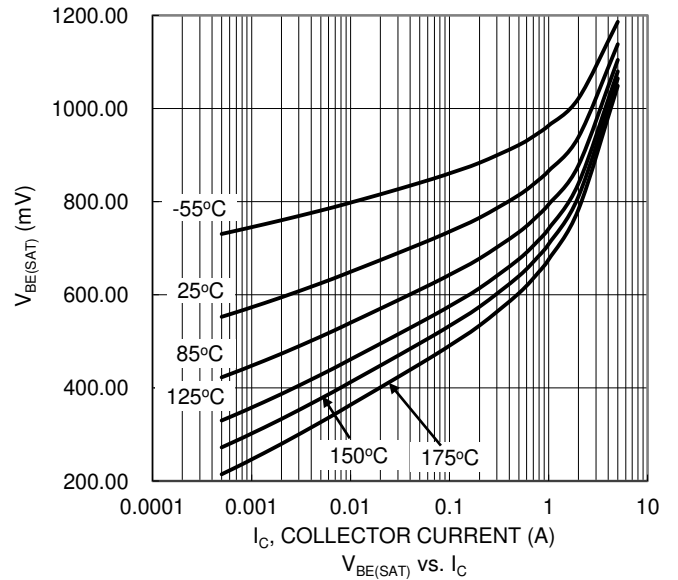
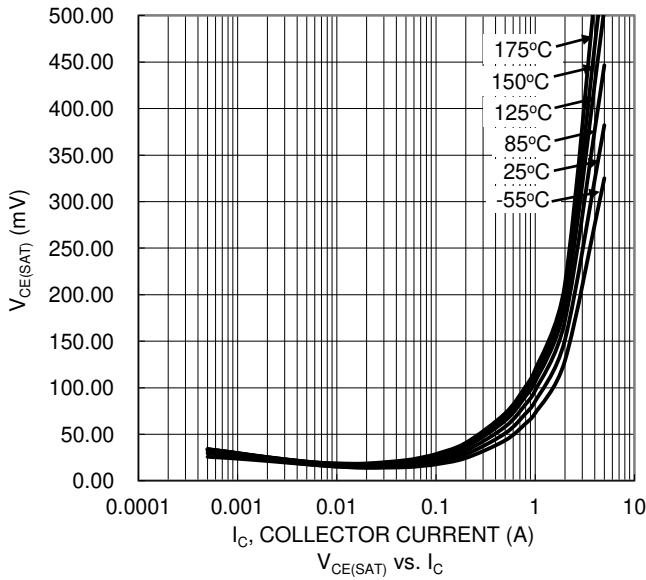


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	120	264	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	129	—	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.4	—	V	I <sub>E</sub> = 100μA
Collector Cut-Off Current	I <sub>CBO</sub>	—	—	50	nA	V <sub>CB</sub> = 100V
		—	—	10	μA	V <sub>CB</sub> = 100V, T <sub>A</sub> = +125°C
Emitter Cut-Off Current	I <sub>EBO</sub>	—	—	20	nA	V <sub>EB</sub> = 6V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(SAT)</sub>	—	90	250	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
		—	150	400	mV	I <sub>C</sub> = 2A, I <sub>B</sub> = 200mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(SAT)</sub>	—	0.86	1	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(ON)</sub>	—	0.79	0.95	V	I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V
DC Current Gain (Note 10)	h <sub>FE</sub>	70	183	—	—	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 2V
		100	172	300	—	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2V
		55	113	—	—	I <sub>C</sub> = 1A, V <sub>CE</sub> = 2V
		25	56	—	—	I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V
Current Gain-Bandwidth Product	f <sub>T</sub>	140	175	—	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 100mA, f = 100MHz
Switching Time	t <sub>ON</sub>	—	80	—	ns	I <sub>C</sub> = 500mA, V <sub>CC</sub> = 10V, I <sub>B1</sub> = -I <sub>B2</sub> = 50mA
	t <sub>OFF</sub>	—	1200	—	ns	
Output Capacitance	C <sub>OBO</sub>	—	—	30	pF	V <sub>CB</sub> = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

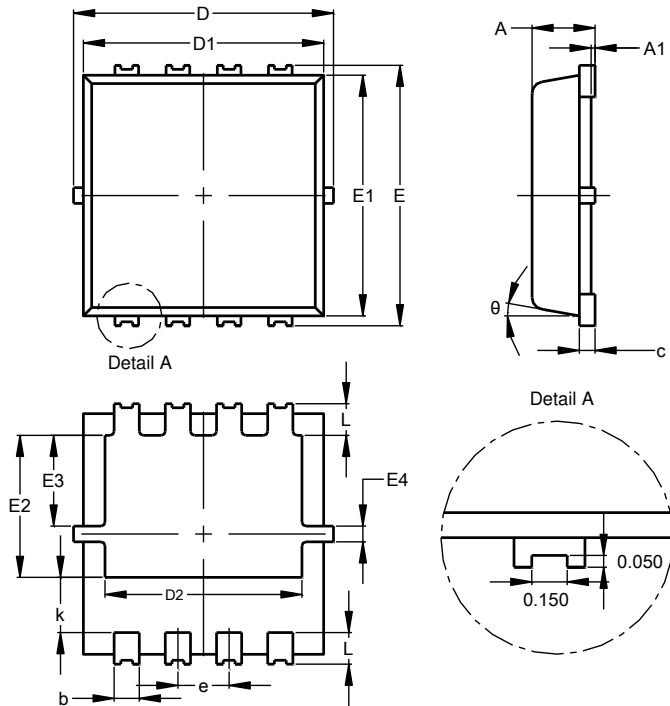
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (SWP) (Type UX)**

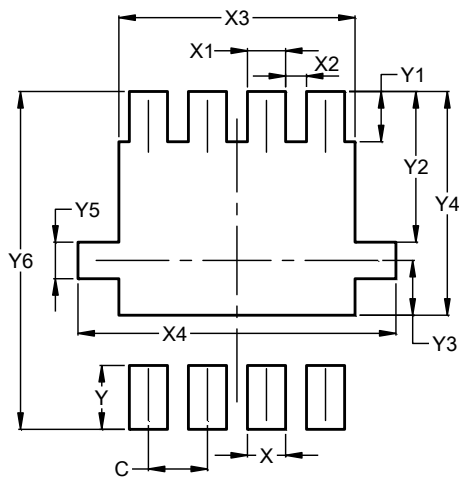


PowerDI3333-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (SWP) (Type UX)**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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